

# SPI

# **4K Bits**

# **Serial EEPROM**

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#### 1. Features

Serial Peripheral Interface (SPI) Compatible

Supports Mode 0 (0,0) and Mode 3 (1,1)

Wide-voltage Operation

- V<sub>CC</sub> = 1.8V to 5.5V

Low power CMOS

— Standby current: ≤1 µA (2.5V)

— Operating current: ≤3 mA (2.5V)

Operating frequency: 10 MHz (5.5V)

Memory organization: 4Kb (512 x 8)

Byte and Page write (up to 16 bytes)

Partial page write allowed

• Block Write Protection

Protect 1/4, 1/2, or Entire Array

Self timed write cycle: 5 ms (max.) @2.5V

High-reliability

Endurance: 1 million cycles

Data retention: 100 years

• Industrial temperature grade

Packages (8-pin): SOIC and TSSOP

• Lead-free, RoHS, Halogen free, Green

### 2. General Description

The GT25C04 is an industrial standard electrically erasable programmable read only memory (EEPROM) product that utilizes standard Serial Peripheral Interface (SPI) for communications. The GT25C04 contains a memory array of 4K bits (512x 8), which is organized in 16 bytes per page.

This EEPROM operates in a wide voltage range from 1.8V to 5.5V, which fits most application. The device provides low-power operations and low standby current. The product is offered in Lead-free, RoHS, halogen free or Green package. The available package types are 8-pin SOIC and TSSOP.

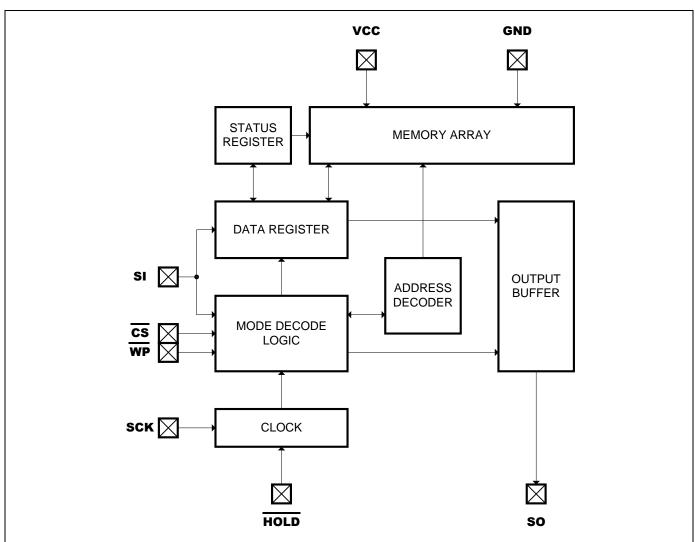
The functionalities of the GT25C04 are optimized for most applications, such as consumer electronics, wireless, telecommunication, industrial, medical, instrumentation, commercial and others, where low-power and low-voltage are vital. This product has a compatible SPI interface: Chip-Select ( $\overline{\text{CS}}$ ), Serial Data In (SI), Serial Data Out (SO) and Serial Clock (SCK) for high-speed communication. Furthermore, a Hold feature via  $\overline{\text{HOLD}}$  pin allows the device entering into a suspended state whenever

necessary and resuming the communication without re-initializing the serial sequence. A Status Register facilitates a flexible write protection mechanism and device status monitoring.

In order to refrain the state machine from entering into a wrong state during power-up sequence or a power toggle off-on condition, a power on reset circuit is implemented. During power-up, the device does not respond to any instructions until the supply voltage (Vcc) has reached an acceptable stable level above the reset threshold voltage. Once V<sub>CC</sub> passes the power on reset threshold, the device is reset and enters into Standby mode. This should also avoid any inadvertent Write operations during power-up stage. During power-down process, the device will enter into standby mode, once Vcc drops below the power on reset threshold voltage. In addition, the device will be in standby mode after receiving the Stop command, provided that no internal write operation is in progress. Nevertheless, it is illegal to send a command unless the Vcc is within its operating level.



### 3. Functional Block Diagram



### **Serial Interface Description**

**Master:** The device that provides a clock signal.

Slave: GT25C04.

Transmitter/Receiver: The GT25C04 has both data input (SI) and data output (SO).

MSB (Most Significant Bit) is the first bit being transmitted or received.

**Op-Code:** Operational instruction code typically sent to the GT25C04 is the first byte of information

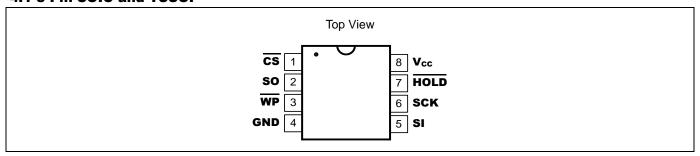
transmitted after  $\overline{\text{CS}}$  is Low. If the Op-Code is a valid instruction as listed in Table 5.3, then it will be

decoded appropriately. It is prohibited to send an invalid Op-Code.



#### 4. Pin Configuration

#### 4.1 8-Pin SOIC and TSSOP



#### 4.2 Pin Definition

Pin No.	Pin Name	I/O	Definition
1	CS	I	Chip Select
2	SO	0	Serial Data Output
3	WP	1	Write Protect Input
4	GND	-	Ground
5	SI	1	Serial Data Input
6	SCK	1	Serial Clock
7	HOLD	I	Hold function
8	Vcc	-	Supply Voltage

#### 4.3 Pin Descriptions

#### Chip Select (CS)

The  $\overline{CS}$  pin is used to enable or disable the device. Upon power-up,  $\overline{CS}$  must follow the supply voltage. When the device is ready for instruction input, this signal requires a High-to-Low transition. Once  $\overline{CS}$  is stable at Low, the device is enabled. Then the master and slave can communicate among each other through SCK, SI, and SO pins. Upon completion of transmission,  $\overline{CS}$  must be driven to High in order to stop the operation or start the internal write operation. And the device will enter into standby mode, unless an internal write operation is in progress. During this mode, SO becomes high impedance.

#### Serial Clock (SCK)

Under the SPI modes (0, 0) and (1, 1), this clock signal provides synchronization between the master and GT25C04. Typically, Op-Codes, addresses and data are latched from SI at the rising edge of SCK, while data from SO are clocked out at the falling edge of SCK.

#### Serial Data Input (SI)

Data Input pin.

#### **Serial Data Output (SO)**

Data output pin.

#### Write Protect ( $\overline{WP}$ )

This active Low input signal is utilized to initiate Hardware Write Protection mode. This mode prevents the Block Protection bits and the WPEN bit in the Status Register from being modified. To activate the Hardware Write Protection, WP must be Low simultaneously when WPEN is set to 1.

#### Hold (HOLD)

This feature is used to suspend the device in the middle of a serial sequence and temporarily ignore further communication on the bus (SI, SO, SCK). The HOLD signal transitions must occur only when SCK is Low and be held stable during SCK transitions. Connecting HOLD to High disables this feature. Figure. 5-8 shows Hold timing.



### 5. Device Operation

#### **5.1 Status Register**

The Status Register accessible by the user consists of 8-bits data for write protection control and write status. It becomes Read-Only under any of the following conditions: Hardware Write Protection is enabled or WEN is set to 0. If neither is true, it can be modified by a valid instruction.

**Table 5.1: Status Register** 

Bit	Symbol	Name	Description			
			When $\overline{RDY} = 0$ , device is ready for an instruction.			
0	RDY	Ready	When $\overline{RDY} = 1$ , device is busy.			
			As busy, device only accepts Read Status Register command.			
			This represents the write protection status of the device.			
			When WEN = 0, Status Register and entire array cannot be modified, regardless			
1	WEN	Write Enable	the setting of WPEN, WP pin or block protection.			
			Write Enable command (WREN) can be used to set WEN to 1.			
			Upon power-up stage, WEN is reset to 0.			
2	BP0	Block Protect Bit	Despite of the status on WPEN, WP or WEN, BP0 and BP1 configure any			
-	DD4	Disab Dastast Dit	combinations of the four blocks being protected (Table 5.2).			
3	BP1	Block Protect Bit	They are non-volatile memory and programmed to 0 by factory.			
4	Х	Don't Care	Values can be either 0 or 1, but are not retained. Mostly always 0, except during			
5	Х	Don't Care	write operation.			
6	Х	Don't Care				
7	Х	Don't Care				

Note: During internal write cycles, bits 0 to 7 are temporarily 1's.

Table 5.2: Block Protection by BP0 and BP1

Lovel	Status Reg	gister Bits	Avvoy Addresses Dystested
Level	BP1	BP0	Array Addresses Protected
0	0 0 0		None
1 (1/4)	0	1	180h-1FFh
2 (1/2)	1	0	100h-1FFh
3 (All)	1	1	000h-1FFh



#### **5.2 Op-Code Instructions**

The operations of the GT25C04 are controlled by a set of instruction Op-Codes (Table 5.3) that are clocked-in serially via SI pin. To initiate an instruction, the chip select  $(\overline{CS})$  must be Low. Subsequently, each Low-to-High transition of the clock (SCK) will latch a stable level from SI. After the 8-bit Op-Code, it may continue to latch-in an address and/or data from SI accordingly, or to output data from SO. During

data output, data are latched out at the falling edge of SCK. All communications start with MSB first. Upon the transmission of the last bit but prior to any following Low-to-High transition on SCK,  $\overline{CS}$  must be brought to High in order to end the transaction and start the operation. The device will enter into Standby Mode after the operation is completed.

Table 5.3: Instruction Op-Codes[1,2,3]

Name	Op-Code	Operation	Address	Data (SI)	Data (SO)
WREN	0000 X110	Set Write Enable Latch	-	-	-
WRDI	0000 X100	Reset Write Enable Latch	-	-	-
RDSR	0000 X101	Read Status Register	-	-	D <sub>7</sub> -D <sub>0</sub> -
WRSR	0000 X001	Write Status Register	-	D <sub>7</sub> -D <sub>0</sub>	-
READ	0000 A <sub>8</sub> 011	Read Data from Array	A <sub>7</sub> -A <sub>0</sub>	-	D <sub>7</sub> -D <sub>0</sub> ,
WRITE	0000 A <sub>8</sub> 010	Write Data to Array	A <sub>7</sub> -A <sub>0</sub>	D <sub>7</sub> -D <sub>0</sub> ,	-

Notes: [1] X = Don't care bit. However, it is recommended to be "0".

#### 5.3 Write Enable

When  $V_{CC}$  is initially applied, the device powers up with both status register and entire array in a write-disabled state. Upon completion of Write Disable (WRDI), Write Status Register (WRSR) or Write Data to Array (WRITE), the device resets the WEN bit in the Status Register to 0. Prior to any data modification, a Write Enable (WREN) instruction is necessary to set WEN to 1 (Figure. 5-2).

#### **5.4 Write Disable**

The device can be completely protected from modification by resetting WEN to 0 through the Write Disable (WRDI) instruction (Figure. 5-3).

#### 5.5 Read Status Register

The Read Status instruction (RDSR) reviews the status of Write Protect Enable, Block Protection setting (Table 5.2), Write Enable state and  $\overline{\text{RDY}}$  status. RDSR is the only instruction accepted when a write cycle is underway. It is recommended that the status of Write Enable and  $\overline{\text{RDY}}$  be checked, especially prior to an attempted modification of

data. These 8 bits information can be repeatedly output on SO after the initial Op-Code (Figure. 5-4).

#### **5.6 Write Status Register**

The Write Status Register instruction (WRSR) allows the user to choose a Block Protection setting and set or reset the WPEN bit. The values of the other data bits incorporated into WRSR can be 0 or 1 and are not stored in the Status Register. WRSR will be ignored unless both following conditions are true: a) WEN = 1, due to a prior WREN instruction; and b) Hardware Write Protection is not enabled (Table 5.4). Except for  $\overline{RDY}$  status, the values in the Status Register remain unchanged until the moment when the write cycle is completed and the register is updated. Note that WPEN can be changed from 1 to 0 only if  $\overline{WP}$  is already set High. Once completed, WEN is reset for complete chip write protection (Fig. 5-5).

#### 5.7 Read Data

This instruction includes an Op-Code and 8-bit address, then results the selected data to be shifted out from SO.

<sup>[2]</sup> Some address bits may be don't care (Table 5.5).

<sup>[3]</sup> It is strongly recommended that an appropriate format of Op-Code must be entered. Otherwise, it may cause unexpected phenomenon to be occurred. Nevertheless, it is illegal to input invalid any Op-Code.





Following the first data byte, additional sequential data can be output. If the data byte of the last address is initially output, then address will rollover to the first address in the array, and the output could loop indefinitely. At any time, a rising  $\overline{\text{CS}}$  signal ceases the operation (Figure. 5-6).

#### 5.8 Write Data

The WRITE instruction contains an Op-Code, a 8-bit address and the first data byte. Additional data bytes may be supplied sequentially after the first byte. Each WRITE instruction can affect up to 16 bytes of data in a page. Each page has a starting address XXXX0000 and an ending address XXXX1111. After the last byte of data in a page is input, the address rolls over to the beginning of the same

page. If more than 16 bytes of data is input during a single instruction, then only the last 16 bytes will be retained, but the initial data will be overwritten.

The contents of the array defined by Block Protection cannot be modified as long as that block configuration is selected. The contents of the array outside the Block Protection can only be modified if Write Enable (WEN) is set to 1. Therefore, it may be necessary that a WREN instruction is initiated prior to WRITE. Once Write operation is completed, WEN is reset for complete chip write protection (Figure. 5-7). Besides, Hardware Write Protection has no affect on the memory array.

**Table 5.4: Write Protection** 

WP	Hardware Write  Protection	WEN	Inside Block	Outside Block	Status Register (WPEN, BP1, BP0)
0	Enabled	Х	Read-only	Read-only	Read-only
1	Not Enabled	0	Read-only	Read-only	Read-only
1	Not Enabled	1	Read-only	Unprotected	Unprotected

Note: X = Don't care bit.

#### Table 5.5: Address Key

Name	GT25C04
A <sub>N</sub>	A <sub>8</sub> -A <sub>0</sub>

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#### 5.9. Diagrams

Figure 5-1. Synchronous Data Timing

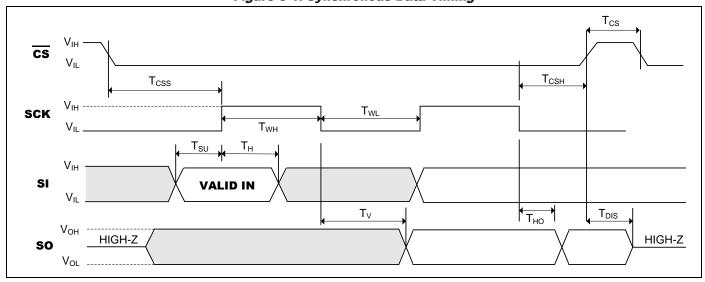


Figure 5-2. WREN Timing

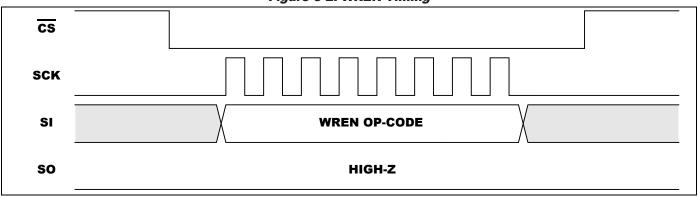


Figure 5-3. WRDI Timing

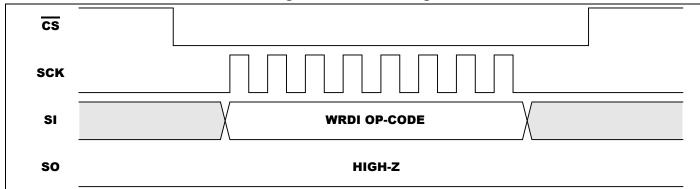




Figure 5-4. RDSR Timing

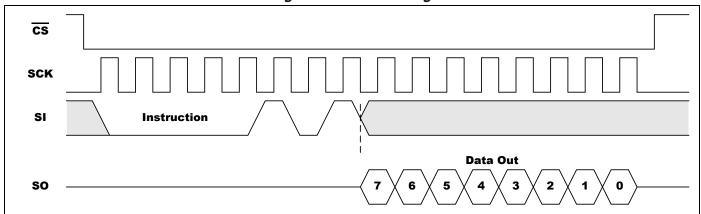


Figure 5-5. WRSR Timing

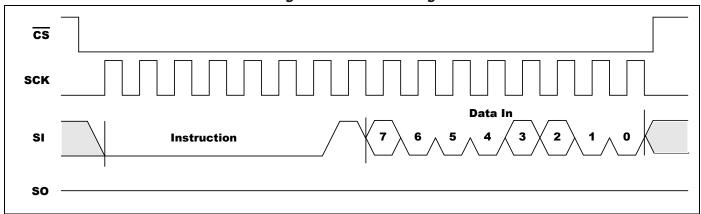


Figure 5-6. READ Timing

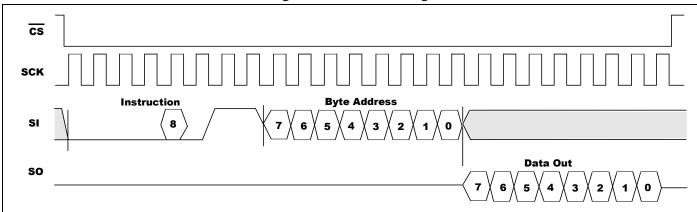




Figure 5-7. WRITE Timing

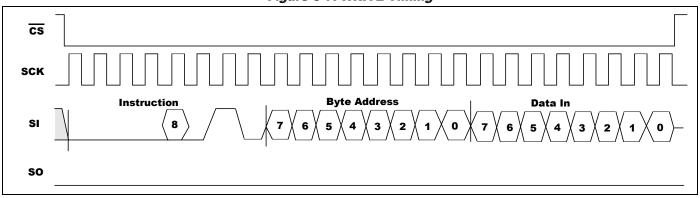
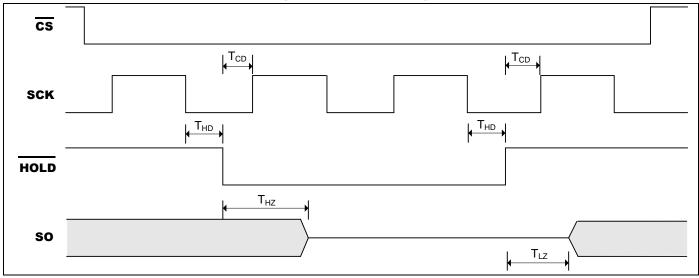


Figure 5-8. HOLD Timing





#### 6. Electrical Characteristics

#### **6.1 Absolute Maximum Ratings**

Symbol	Parameter	Value	Unit
Vs	Supply Voltage	-0.5 to + 6.5	V
V <sub>P</sub>	Voltage on Any Pin	-0.5 to + 6.5	V
T <sub>BIAS</sub>	Temperature Under Bias	-55 to +125	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C
Іоит	Output Current	5	mA

Note: Stress greater than those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other condition outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

#### **6.2 Operating Range**

Range	Ambient Temperature (T <sub>A</sub> )	Vcc	
Industrial	-40°C to +85°C	1.8V to 5.5V	

Note: Giantec offers Industrial grade for Commercial applications (0°C to +70°C).

#### 6.3 Capacitance

Symbol	Parameter <sup>[1, 2]</sup>	Conditions	Max.	Unit
C <sub>IN</sub>	Input Capacitance	$V_{IN} = 0V$	6	pF
C <sub>I/O</sub>	Input / Output Capacitance	$V_{I/O} = 0V$	8	pF

Notes: [1] Tested initially and after any design or process changes that may affect these parameters and not 100% tested.

 $<sup>^{\</sup>text{[2]}}$  Test conditions:  $T_{\text{A}}$  = 25°C, f = 1 MHz,  $V_{\text{CC}}$  = 5.0V





#### **6.4 DC Electrical Characteristic**

Industrial:  $T_A = -40$ °C to +85°C,  $V_{cc} = 1.8V \sim 5.5V$ 

Symbol	Parameter	Vcc	Test Conditions	Min.	Max.	Unit	
Vcc	Supply Voltage			1.8	5.5	V	
VIH	Input High Voltage			0.7* Vcc	Vcc+1	V	
VIL	Input Low Voltage			-0.3	0.3* Vcc	V	
lы	Input Leakage Current		V <sub>IN</sub> = 0V To V <sub>CC</sub>	-2	2	μA	
ILO	Output Leakage Current		V <sub>OUT</sub> = 0V To V <sub>CC</sub> , $\overline{CS}$ = V <sub>CC</sub>	-2	2	μA	
		1.8	Iон = -0.1mA	0.8*Vcc	_	V	
Vон	Output High Voltage	/он Output High Voltage		Iон = -0.4mA	0.8*Vcc	_	V
		5	lон = -2 mA	0.8*Vcc	_	V	
		1.8	I <sub>OL</sub> = 0.15 mA	_	0.2	V	
Vol	Output Low Voltage	2.5	I <sub>OL</sub> = 1.5 mA	_	0.4	V	
		5	I <sub>OL</sub> = 2 mA	_	0.4	V	
		1.8	Read/Write at 2 MHz, SO=Open	_	1	mA	
Icc	Operating Current	2.5	Read/Write at 5 MHz, SO=Open	_	3	mA	
		5	Read/Write at 10 MHz, SO=Open	_	5	mA	
		1.8	V <sub>IN</sub> = V <sub>CC</sub> or GND, $\overline{CS}$ = V <sub>CC</sub>	_	0.5	μΑ	
I <sub>SB</sub>	Standby Current	2.5	$V_{IN} = V_{CC}$ or $GND$ , $\overline{CS} = V_{CC}$		1	μA	
		5	$V_{IN} = V_{CC}$ or $GND$ , $\overline{CS} = V_{CC}$		2	μA	



#### **6.5 AC Electrical Characteristic**

Industrial:  $T_A = -40$ °C to +85°C, Supply voltage = 1.8V to 5.5V

0hl	Parameter <sup>[1]</sup>	1.8V≤V	cc< <b>2.5V</b>	2.5V≤V	cc<4.5V	4.5V≤V	4.5V≤Vcc≤5.5V	
Symbol		Min.	Max.	Min.	Max.	Min.	Max.	Unit
Fsck	SCK Clock Frequency	0	2	0	5	0	10	MHz
T <sub>RI</sub>	Input Rise Time	_	2	_	2	_	2	μs
T <sub>FI</sub>	Input Fall Time	_	2	_	2	_	2	μs
Тwн	SCK High Time	200	_	90	_	40	_	ns
TwL	SCK Low Time	200	_	90	_	40	_	ns
Tcs	CS High Time	200	_	100	_	40	_	ns
Tcss	CS Setup Time	200	_	90	_	40	_	ns
Tcsh	CS Hold Time	200	_	90	_	40	_	ns
Tsu	Data In Setup Time	40	_	20	_	15	_	ns
Тн	Data In Hold Time	50	_	30	_	15	_	ns
$T_{HD}$	HOLD Setup Time	100	_	50	_	25	_	ns
T <sub>CD</sub>	HOLD Hold Time	100	_	50	_	25	_	ns
T <sub>V</sub> [2]	Output Valid	0	150	0	60	0	25	ns
Тно	Output Hold Time	0	_	0	_	0	_	ns
T <sub>LZ</sub>	HOLD to Output Low Z	0	100	0	50	0	25	ns
T <sub>HZ</sub>	HOLD to Output High Z		250		100		25	ns
T <sub>DIS</sub>	Output Disable Time	_	250	_	100	_	25	ns
Twc	Write Cycle Time		10	_	5		5	ms

Notes: [1] The parameters are characterized but not 100% tested.

 $<sup>^{[2]}</sup>C_L = 100pF \text{ (typical)}$ 



### 7. Ordering Information

#### Industrial Grade: -40°C to +85°C, Lead-free

Voltage Range	Part Number*	Package (8-pin)*
1.8V to 5.5V	GT25C04-2GLI-TR	150-mil SOIC
	GT25C04-2ZLI-TR	3 x 4.4 mm TSSOP

1. Contact Giantec Sales Representatives for availability and other package information.

- 2. The product is packed in tape and reel "-TR" (4K per reel), except UDFN is 5K per reel.
- 3. Refer to Giantec website for related declaration document on lead free, RoHS, halogen free or Green, whichever is applicable.
- 4. Giantec offers Industrial grade for Commercial applications (0°C to +70°C).



### 8. Top Markings

#### 8.1 SOIC Package



G: Giantec Logo

504-2GLI: GT25C04-2GLI-TR

YWW: Date Code, Y=year, WW=week

#### 8.2 TSSOP Package



GT: Giantec Logo

504-2<u>Z</u>LI: GT25C04-2ZLI-TR

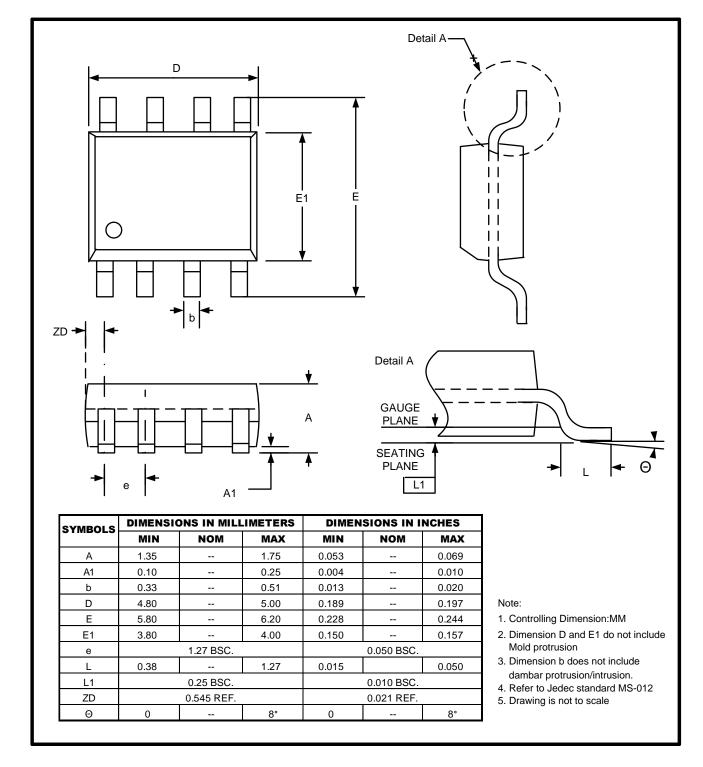
YWW: Date Code, Y=year, WW=week



#### 9. Package Information

#### 9.1 **SOIC**

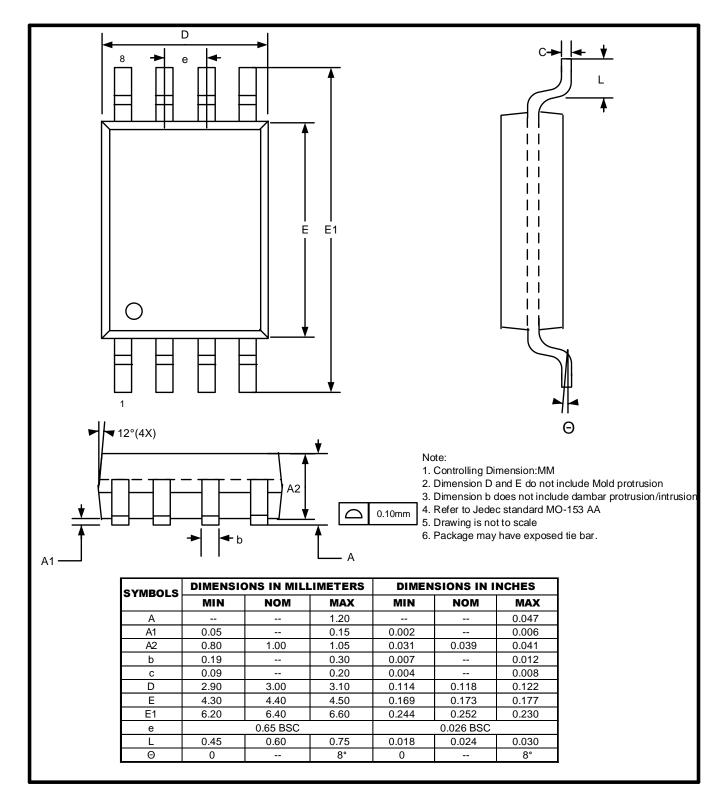
#### **8L 150mil SOIC Package Outline**





#### **9.2 TSSOP**

#### 8L 3x4.4mm TSSOP Package Outline





### 10. Revision History

Revision	Date	Descriptions
A0	Jan. 2010	Initial version
A1	Jun. 2011	New datasheet format
C2	Oct. 2013	Revise SOIC/SOP to SOIC
D3	Jul. 2016	Update TSSOP top mark
C4	Jul. 2019	Update TSSOP POD and VP